

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-7. (Canceled).

8. (Currently Amended) A method of manufacturing a ~~transistor~~ transistor, the method comprising:

~~\_\_\_\_\_ preparing a substrate;~~  
forming a semiconductor film on the substrate;  
forming a ~~first region in the plurality of third regions in the~~ semiconductor film ~~by applying by a first ion doping of a first impurity atom to the semiconductor film; of a~~  
second conduction type, each of the plurality of third regions being separated by a space;  
forming an insulator film over the semiconductor film;  
forming a gate electrode over the insulator film; and  
forming a ~~second and a third region in the~~ first region and a second region in  
the semiconductor film by applying a second impurity atom to the semiconductor film after  
the forming of the first region, film by a second ion doping of a second impurity of a first  
conduction type,  
~~\_\_\_\_\_ the second and the third region being separated by the first region, and the first~~  
~~impurity atom and the second impurity atom being different.~~ the gate electrode overlapping at  
least a part of each of the plurality of the third regions, and the plurality of third regions  
located between the first region and the second region.

9. (Currently Amended) The method of manufacturing a transistor according to claim 8,

the semiconductor film having a channel region under the gate electrode, the channel region not including any of the first ~~and impurity of the second impurity~~ atom-conduction type and the second impurity of a first conduction type.

10-14. (Canceled).

15. (Currently Amended) The method of manufacturing a transistor according to claim 8, further comprising:

applying an energy to the semiconductor film to crystallize the semiconductor film before the forming of the ~~third region~~ second region.

16. (Currently Amended) The method of manufacturing a transistor according to claim 8, further comprising:

forming a source and a drain electrode, the source electrode being connected to the first ~~region~~ region in the semiconductor film, the drain electrode being connected to the second ~~region~~ region in the semiconductor film, and none of the source and the drain electrodes being connected to the ~~first region~~ plurality of third regions.

17. (Previously Presented) A method of manufacturing an active-matrix substrate using the method of manufacturing a transistor according to claim 8.

18. (Previously Presented) A method of manufacturing an electroluminescent device using the method of manufacturing a transistor according to claim 8.

19. (Previously Presented) A method of manufacturing a display device using the method of manufacturing a transistor according to claim 8.

20. (Previously Presented) A method of manufacturing an electronic apparatus using the method of manufacturing a transistor according to claim 8.

21. (New) A method of manufacturing a transistor, the method comprising:

forming a semiconductor film in a substrate;

forming an insulator film over the semiconductor film;

forming a gate electrode over the insulator film; and

forming a third region in the semiconductor film by a first ion doping of a first impurity of a second conduction type; and

forming a first region and a second region in the semiconductor film by a second ion doping of a second impurity of a first conduction type, a dosage of the second impurity being smaller than a dosage of the first impurity, the third region including a first part, a second part, and a channel region disposed between the first part and the second part, the first part being located between the first region and the channel region, and the second part being located between the second region and the channel region.

22. (New) The method of manufacturing a transistor according to claim 8, a dosage of the second impurity being smaller than a dosage of the first impurity.

23. (New) The method of manufacturing a transistor according to claim 21, the channel region not including any of the first impurity and the second impurity.

24. (New) The method of manufacturing a transistor according to claim 21, further comprising:

applying an energy to the semiconductor film to crystallize the semiconductor film before the forming of the second region.

25. (New) The method of manufacturing a transistor according to claim 21, further comprising:

forming a source and a drain electrode, the source electrode being connected to the first region in the semiconductor film, the drain electrode being connected to the second

region in the semiconductor film, and none of the source and the drain electrodes being connected to the third region.

26. (New) A method of manufacturing an active-matrix substrate using the method of manufacturing a transistor according to claim 21.

27. (New) A method of manufacturing an electroluminescent device using the method of manufacturing a transistor according to claim 21.

28. (New) A method of manufacturing a display device using the method of manufacturing a transistor according to claim 21.

29. (New) A method of manufacturing an electronic apparatus using the method of manufacturing a transistor according to claim 21.

30. (New) The method of manufacturing a transistor according to claim 8, the first region having a first end and a second end in opposite sides of the first region, the first end of the first region being in a side opposite the plurality of third regions, the second region having a first end and a second end in opposites sides of the second region, the first end of the second region being in a side opposite the plurality of third regions.

31. (New) The method of manufacturing a transistor according to claim 30, the first end of the first region and the first end of the second region each having a width more narrow than a width of the plurality of third regions.

32. (New) The method of manufacturing a transistor according to claim 31, the width of the plurality of third regions being about 20 mm larger than the width of either of the first end of the first region and the first end of the second region.